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STATEMENT BY APPLICANT

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Attorney Docket Number 45368/MJM/A717

Application Number 09/516,004

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Group Art Unit 2811

Examiner Name O. Nadav

U.S. PATENT DOCUMENTS

EXAMINER INITIALS	Cite No. <sup>1</sup>	DOCUMENT NUMBER Number - kind code <sup>2</sup> . (If known)	PUBLICATION DATE MM-DD-YYYY	NAME OF PATENTEE
ON		5,696,011	12-09-1997	Yamazaki et al.
ON		5,953,615	09-14-1999	Yu

FOREIGN PATENT DOCUMENTS

EXAMINER INITIALS	Cite No. <sup>1</sup>	Foreign Patent Document Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> (If known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	T <sup>6</sup> (✓)
ON		Taiwan Patent Publication No. 305063			English Translation Only

OTHER DOCUMENTS

EXAMINER INITIALS	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article, title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
ON		AUTRAN J-L, et al., "Fabrication and Characterization of SI-MOSFET'S with PECVD Amorphous Ta <sub>2</sub> O <sub>5</sub> Gate Insulator", September 1, 1997, pages 447-449, Vol. 18, No. 9, IEEE, New York, US
ON		CHANELIERE C, et al., "Tantalum Pentoxide (Ta <sub>2</sub> O <sub>5</sub> ) Thin Films for Advanced Dielectric Applications", May 25, 1998, pages 269-322, Vol. 22, No. 6, Materials Science and Engineering R: Reports, Elsevier Sequoia S.A., Lausanne, CH

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